

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI SD1492** is a Common Emitter Device Designed for Class AB operation in UHF Amplifier Applications in Television Band IV & V Transmitters.

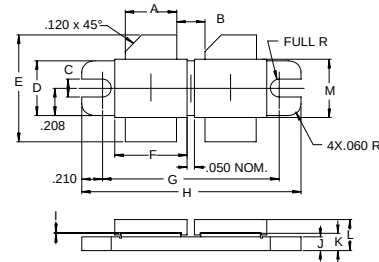
FEATURES INCLUDE:

- Gold Metalization
- Emitter Ballasting
- Internal Matching

MAXIMUM RATINGS

I_C	25 A
V_{CBO}	60 V
P_{DISS}	310 W @ $T_C = 25\text{ }^{\circ}\text{C}$
T_J	-65 $^{\circ}\text{C}$ to +200 $^{\circ}\text{C}$
T_{STG}	-65 $^{\circ}\text{C}$ to +150 $^{\circ}\text{C}$
θ_{JC}	0.55 $^{\circ}\text{C/W}$

PACKAGE STYLE .450 BAL FLG.(A)



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.373 / 9.47	.385 / 9.78
B	.205 / 5.21	
C	.120 / 3.25	.130 / 3.30
D	.411 / 10.44	.421 / 10.69
E	.825 / 20.96	.865 / 21.97
F	.525 / 13.34	.535 / 13.59
G	1.255 / 31.88	1.265 / 32.18
H	1.675 / 42.55	1.685 / 42.80
I	.002 / 0.05	.006 / 0.15
J	.095 / 2.41	.105 / 2.67
K	.115 / 2.92	.135 / 3.43
L		.250 / 6.35
M	.445 / 11.30	.457 / 11.61

CHARACTERISTICS $T_C = 25\text{ }^{\circ}\text{C}$

SYMBOL	TEST CONDITIONS (PER SIDE)	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 100\text{ mA}$	30			V
BV_{CBO}	$I_C = 100\text{ mA}$	60			V
BV_{EBO}	$I_E = 50\text{ mA}$	3.0			V
I_{CES}	$V_{CE} = 28\text{ V}$			10	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 3.0\text{ A}$	15		70	---
C_{OB}	$V_{CB} = 28\text{ V}$ $f = 1.0\text{ MHz}$			100	pF
P_{OUT}	$V_{CE} = 28\text{ V}$ $I_{CQ} = 2 \times 500\text{ mA}$ $f = 860\text{ MHz}$	150			W
G_P	$V_{CE} = 28\text{ V}$ $I_{CQ} = 2 \times 250\text{ mA}$ $f = 860\text{ MHz}$	6.5			dB
n_C	$P_{out} = 150\text{ W}$	45			dBc